

MA6X123

Silicon epitaxial planar type

For switching circuit

■ Features

- Four-element contained in one package, allowing high-density mounting
- Centrosymmetrical wiring, allowing to free from the taping direction
- Short reverse recovery time t_{rr}
- Small terminal capacitance, C_t

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	80	V
Peak reverse voltage	V_{RM}	80	V
Average forward current ^{*1}	I_F	100	mA
Peak forward current ^{*1}	I_{FM}	225	mA
Non-repetitive peak forward surge current ^{*1,2}	I_{FSM}	500	mA
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Note) *1 : Value for single diode

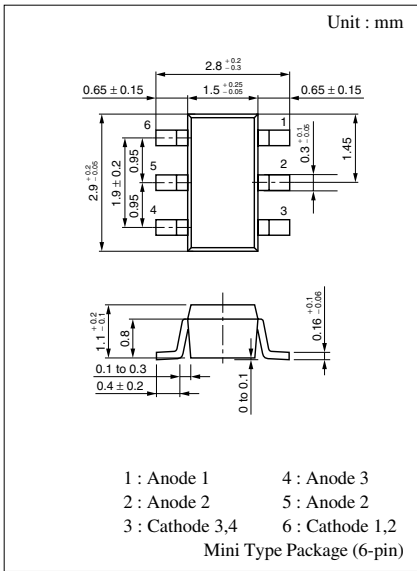
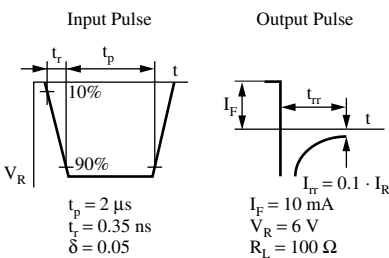
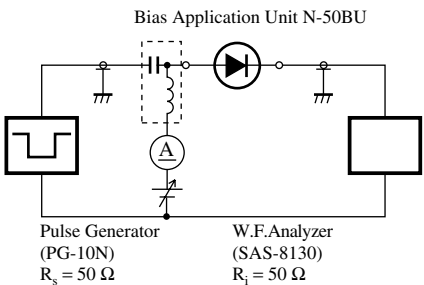
*2 : $t = 1 \text{ s}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	I_R	$V_R = 75 \text{ V}$			100	nA
Forward voltage (DC)	V_F	$I_F = 100 \text{ mA}$			1.2	V
Reverse voltage (DC)	V_R	$I_R = 100 \mu\text{A}$	80			V
Terminal capacitance	C_t	$V_R = 0 \text{ V}, f = 1 \text{ MHz}$			2	pF
Reverse recovery time [*]	t_{rr}	$I_F = 10 \text{ mA}, V_R = 6 \text{ V}$ $I_{rr} = 0.1 \cdot I_R, R_L = 100 \Omega$			3	ns

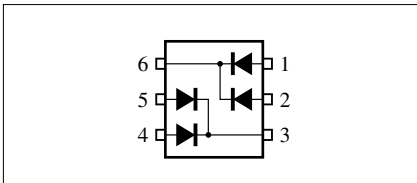
Note) 1. Rated input/output frequency: 100 MHz

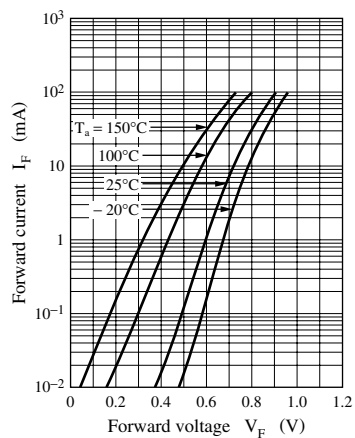
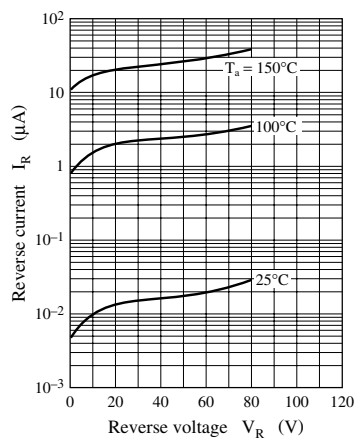
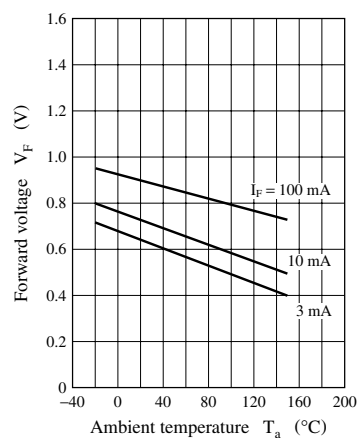
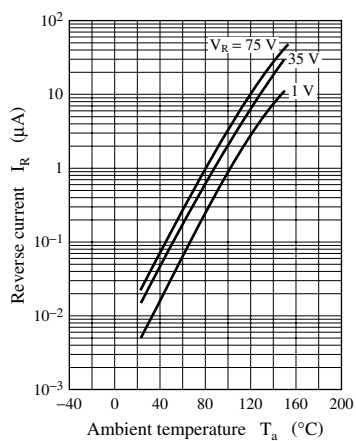
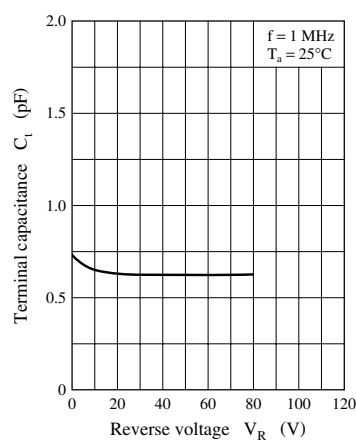
2. * : t_{rr} measuring circuit



Marking Symbol: M2B

Internal Connection



$I_F - V_F$  $I_R - V_R$  $V_F - T_a$  $I_R - T_a$  $C_t - V_R$  $I_{F(\text{surge})} - t_w$ 